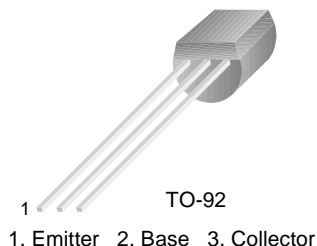


KSP8098/8099

KSP8098/8099

Amplifier Transistor

- Collector-Emitter Voltage: V_{CE0} = KSP8098: 60V
KSP8099: 80V
- Collector Power Dissipation: P_C (max)=625mW
- Suffix "-C" means Center Collector (1. Emitter 2. Collector 3. Base)



NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_a=25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Value | Units |
|-----------|-----------------------------|-----------|------------------|
| V_{CBO} | Collector-Base Voltage | : KSP8098 | 60 |
| | | : KSP8099 | 80 |
| V_{CE0} | Collector-Emitter Voltage | : KSP8098 | 60 |
| | | : KSP8099 | 80 |
| V_{EBO} | Emitter-Base Voltage | 6 | V |
| I_C | Collector Current | 500 | mA |
| P_C | Collector Power Dissipation | 625 | mW |
| T_J | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{STG} | Storage Temperature | -55 ~ 150 | $^\circ\text{C}$ |

Electrical Characteristics $T_a=25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Max. | Units |
|----------------------|---------------------------------------|---|-----------|------|-------|
| BV_{CBO} | Collector-Base Breakdown Voltage | $I_C=100\mu\text{A}, I_E=0$ | : KSP8098 | 60 | V |
| | | | : KSP8099 | 80 | V |
| BV_{CE0} | * Collector-Emitter Breakdown Voltage | $I_C=10\text{mA}, I_B=0$ | : KSP8098 | 60 | V |
| | | | : KSP8099 | 80 | V |
| BV_{EBO} | Emitter-Base Breakdown Voltage | $I_E=10\mu\text{A}, I_C=0$ | 6 | | V |
| I_{CBO} | Collector Cut-off Current | $V_{CB}=60\text{V}, I_E=0$ $V_{CB}=80\text{V}, I_E=0$ | | 100 | nA |
| | | | | 100 | nA |
| I_{CEO} | Collector Cut-off Current | $V_{CE}=60\text{V}, I_B=0$ | | 100 | nA |
| I_{EBO} | Emitter Cut-off Current | $V_{EB}=6\text{V}, I_C=0$ | | 100 | nA |
| h_{FE} | DC Current Gain | $V_{CE}=5\text{V}, I_C=1\text{mA}$ $V_{CE}=5\text{V}, I_C=10\text{mA}$ $V_{CE}=5\text{V}, I_C=100\text{mA}$ | 100 | 300 | |
| | | | 100 | | |
| | | | 75 | | |
| $V_{CE}(\text{sat})$ | Collector-Emitter Saturation Voltage | $I_C=100\text{mA}, I_B=5\text{mA}$ $I_C=100\text{mA}, I_B=10\text{mA}$ | | 0.4 | V |
| | | | | 0.3 | V |
| $V_{BE}(\text{on})$ | * Base-Emitter On Voltage | $V_{CE}=5\text{V}, I_C=1\text{mA}$ $V_{CE}=5\text{V}, I_C=10\text{mA}$ | : KSP8098 | 0.5 | 0.7 |
| | | | : KSP8099 | 0.6 | 0.8 |
| f_T | Current Gain Bandwidth Product | $V_{CE}=5\text{V}, I_C=10\text{mA}$ $f=100\text{MHz}$ | 150 | | MHz |
| C_{ob} | Output Capacitance | $V_{CB}=5\text{V}, I_E=0$ $f=1\text{MHz}$ | | 6 | pF |

* Pulse Test: Pulse Width \leq 300 μs , Duty Cycle \leq 2%

Typical Characteristics

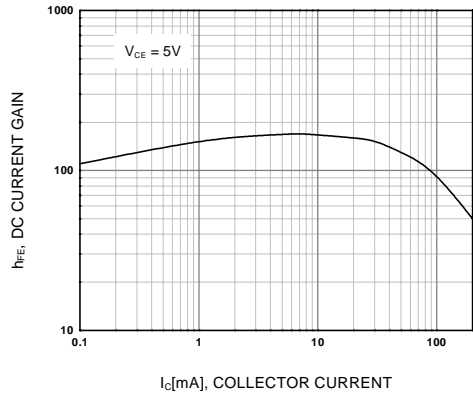


Figure 1. DC current Gain

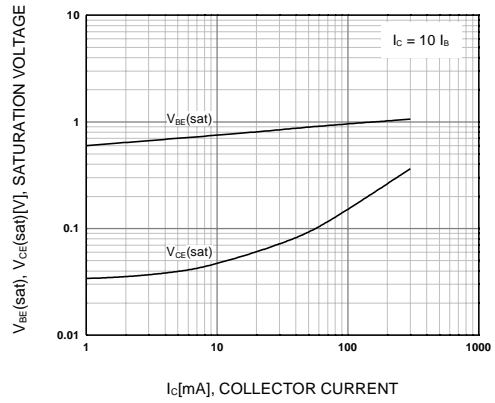


Figure 2. Collector-Emitter Saturation Voltage
Base-Emitter Saturation Voltage

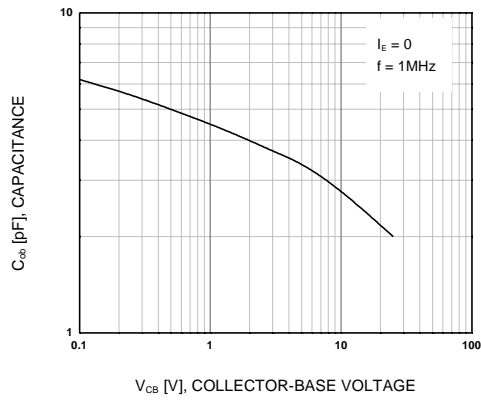


Figure 3. Output Capacitance

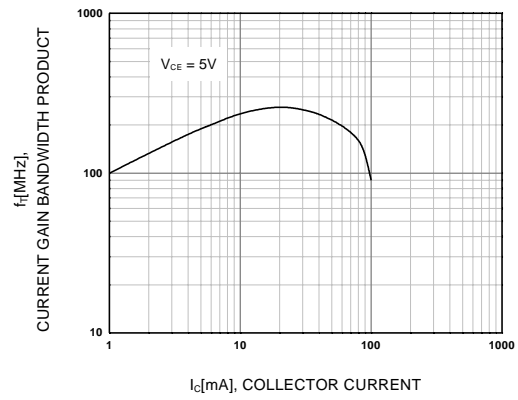


Figure 4. Current Gain Bandwidth Product

Package Dimensions

TO-92

KSP8098/8099



Dimensions in Millimeters

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